

December 2020: END SEMESTER ASSESSMENT B Tech III SEMESTER

UE19EC204 - ANALOG CIRCUIT DESIGN

Time: 3 Hrs	Answer All Questions	Max Marks: 100
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1.	a)	With neat circuit diagram obtain an expression to avoid saturation region operation of transistor in simple biasing technique. Further, also specify any one limitation of this technique.	4
	b)	We wish to design a circuit that exhibits the input/output characteristic shown in Figure 1. Using $1\text{k}\Omega$ resistors, ideal diodes, and other components, construct the circuit.	5
		<p style="text-align: center;">Figure 1</p>	
	c)	With relevant waveforms, explain emitter follower circuit as a power amplifier.	5
	d)	In the circuit of Figure 2, determine the required value of R_E . Assume collector current equal to 0.5mA , $\beta = 100$ and $I_S = 5 \times 10^{-15}\text{A}$.	6
		<p style="text-align: center;">Figure 2</p>	
2.	a)	Write a short note on CMOS technology	4
	b)	From the fundamentals of channel charge density derive an expression for drain current in the MOSFET	6
	c)	Write importance differences between NMOS and PMOS transistors	4
	d)	A MOSFET is biased at a drain current of 0.5mA . If $\mu_n C_{ox} = 100\text{ }\mu\text{A/V}^2$, $W/L = 10$, and $\lambda = 0.1\text{V}^{-1}$, $\eta = 0.1$, calculate its small-signal parameters.	6

